

## EPIGAP Optronic GmbH

Koepenicker Str. 325b  
D-12555 Berlin  
Fon: +49 (0)30 657637 60  
Fax: +49 (0)30 657637 70



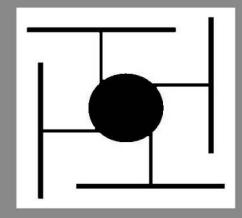
## Data Sheet

### LED Chip deep red

### EOLC-660-15

Rev. 02, 2014

Radiation	Type	Electrodes
deep red	AlGaAs	n (cathode) up

	<ul style="list-style-type: none"> <li>- High luminous intensity</li> <li>- Thin film structure</li> <li>- Typ. chip size <math>340 \pm 25 \mu\text{m}</math></li> <li>- Typ. thickness <math>225 \pm 25 \mu\text{m}</math></li> </ul>
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#### Absolute Maximum Ratings

$T_{\text{amb}} = 25^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Typ	Unit
Forward DC current	$I_F$	$\leq 70$	mA
Reverse voltage	$V_R$	$\leq 10$	V
Junction temperature	$T_J$	125	$^\circ\text{C}$
Storage temperature	$T_{\text{stg}}$	-40 ~ +85	$^\circ\text{C}$

#### Optical and Electrical Characteristics

$T_{\text{amb}} = 25^\circ\text{C}$ , unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F=10 \mu\text{A}$	$V_F$	1.3			V
Forward voltage	$I_F=20 \text{ mA}$	$V_F$		2.1	2.5	V
Reverse current	$V_R = 10\text{V}$	$I_R$			5	$\mu\text{A}$
Output power	$I_F=20 \text{ mA}$	$I_V$		9		mW
Peak wavelength	$I_F=20 \text{ mA}$	$\lambda_p$	650	660	670	nm
Spectral bandwidth at 50%	$I_F=20 \text{ mA}$	$\Delta\lambda_{0.5}$		20		nm



We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.